Panasonic

UP05C8GG

Silicon NPN epitaxial planar type (Tr) Silicon epitaxial planar type (CCD load device)

For CCD output circuits

■ Features

- Two elements incorporated into one package (Tr + CCD load device)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

■ Basic Part Number

• 2SC3932G + CCD load device

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter		Symbol	Rating	Unit	
Tr	Collector-base voltage (Emitter open)	V _{CBO}	30	V	
	Collector-emitter voltage (Base open)	V _{CEO}	20	V	
	Emitter-base voltage (Collector open)	V _{EBO}	3	V	
	Collector current	I_{C}	50	mA	
CCD load device	Limiting element voltage	V _{max} 40		V	
	Limiting element current	I _{max}	10	mA	
Overall	Total power dissipation *	P_{T}	125	mW	
	Junction temperature	T _j	125	°C	
	Storage temperature	T _{stg}	-55 to +125	°C	

Note) * : Measuring on substrate at 17 mm \times 10 mm \times 1 mm

■ Package

• Code

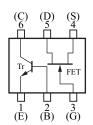
SSMini6-F2

• Pin Name

1: Emitter 4: Source 2: Base 5: Drain 3: Gate 6: Collector

■ Marking Symbol: 4V

■ Internal Connection



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■ Electrical Characteristics $T_a = 25$ °C±3°C

• T

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 100 \mu A, I_E = 0$	30			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	3			V
Base-emitter voltage	V_{BE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		720		mV
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	25		250	_
Transition frequency *	f_T	$V_{CB} = 10 \text{ V}, I_E = -15 \text{ mA}, f = 200 \text{ MHz}$	800		1200	MHz
Power gain	PG	$V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		20		dB

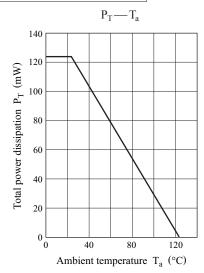
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• CCD Load Device

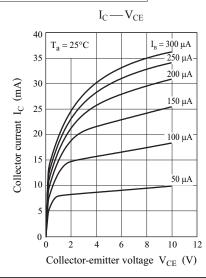
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Pinchi off current	I_P	$V_{DS} = 10 \text{ V}, V_G = 0$	3.5		5.5	mA
Output impedance	Zo	$V_{DS} = 10 \text{ V}, V_G = 0$		0.05		ΜΩ

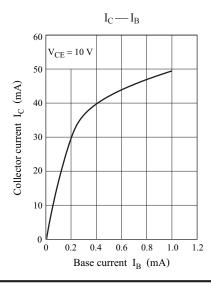
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

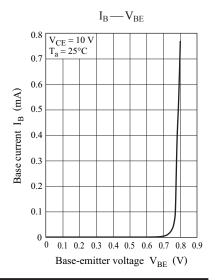
Common characteristics chart



Characteristics charts of Tr



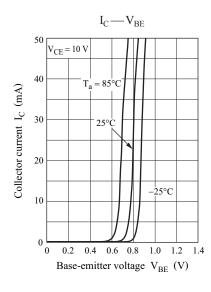


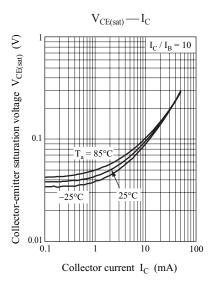


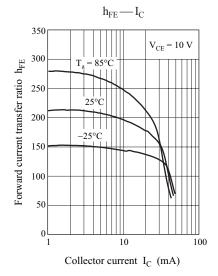
2 SJJ00400BED

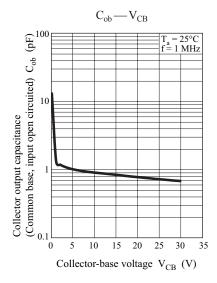
^{*:} Pulse measurement

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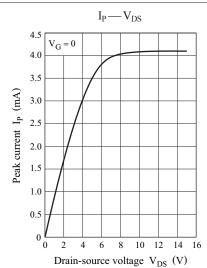








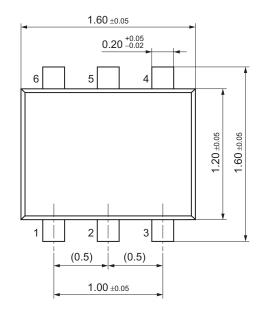
Characteristics charts of CCD load device

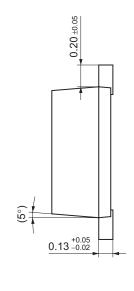


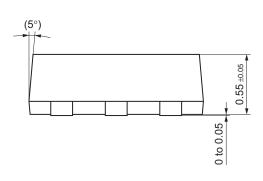
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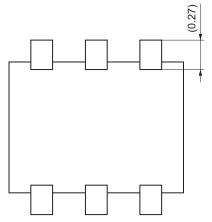
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SSMini6-F2 Unit: mm









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